Ordering number: ENN6429

N-Channel Silicon MOSFET



FTD2005

# **Ultrahigh-Speed Switching Applications**

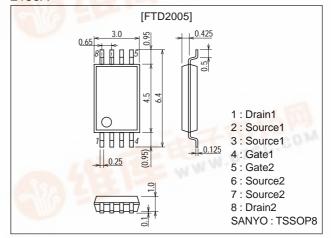
#### **Features**

- · Low ON resistance.
- · 2.5V drive.
- · Mounting height 1.1mm.
- · Composite type, facilitating high-density mounting.

### **Package Dimensions**

unit:mm

2155A



# **Specifications**

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V	
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V	
Drain Current (DC)	ID		1	Α	
Drain Current (pulse)	I <sub>DP</sub>	PW≤10µs, duty cycle≤1%	4	Α	
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (1000mm <sup>2</sup> ×0.8mm) 1unit	0.8	W	
Total Dissipation	PT	Mounted on a ceramic board (1000mm²×0.8mm)	1.0	W	
Channel Temperature	Tch	AND ARE THE W	150	°C	
Storage Temperature	Tstg	The second secon	-55 to +150	°C	

#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			10	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	1.8	2.6	3 3 1 1	S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>GS</sub> =4V	m.,	200	260	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V	- W	260	360	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		90		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		28		pF

Marking: D2005

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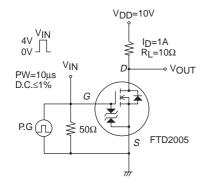
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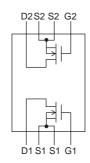
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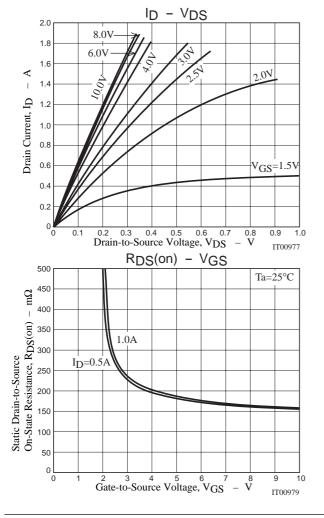
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Turn-ON Delay Time	t <sub>d</sub> (on)	See Specified Test Circuit		10		ns
Rise Time	t <sub>r</sub>	See Specified Test Circuit		22		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See Specified Test Circuit		20		ns
Fall Time	t <sub>f</sub>	See Specified Test Circuit		19		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A		6		nC
Gate-to-Source Charge	Qgs			1		nC
Gate-to-Drain "Miller" Charge	Qgd			2		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0		1.0	1.2	V

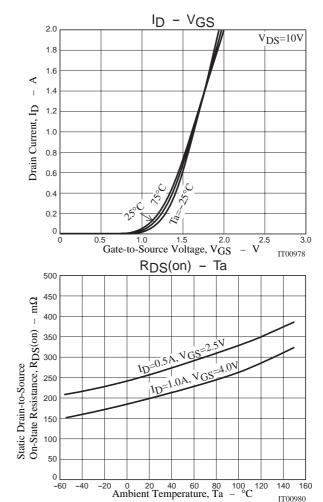
### **Switching Time Test Circuit**



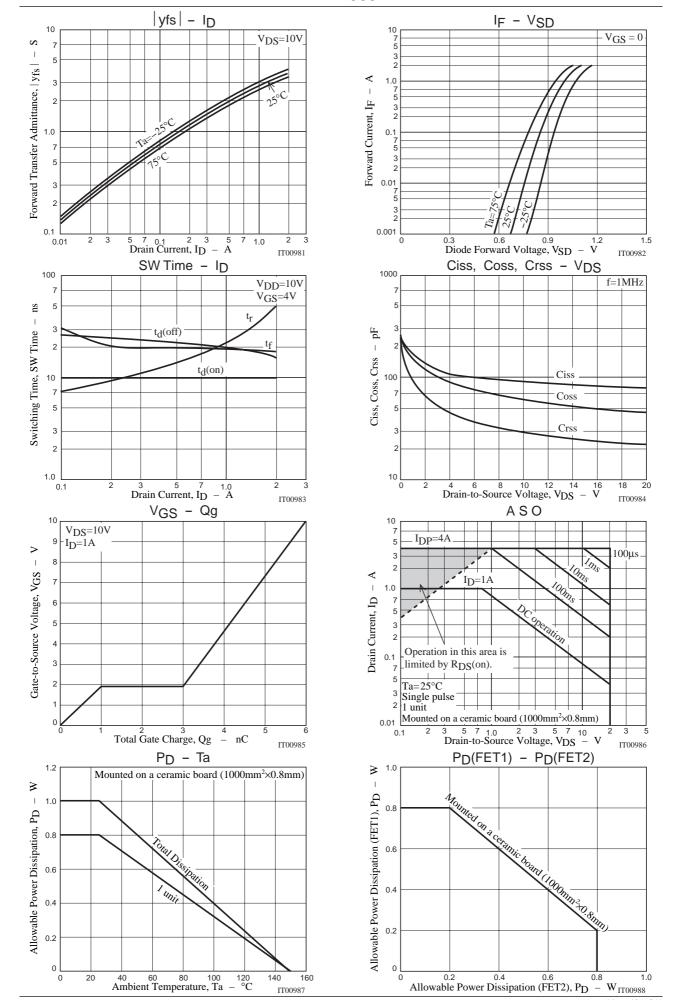
### **Electrical Connection**







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